



Photodiode

EPD-880-5/0.9

Prototype

05.2007

rev. 01/07

Wavelength	Type	Technology	Case
Infrared	Integrated filter	AlGaAs/GaAs	5 mm plastic lens

	<p>Description Selective photodiode mounted in standard 5 mm package without standoff. Narrow bandwidth and high spectral sensitivity in the infrared range (810...950 nm).</p> <p>Note: Special packages with standoff available on request</p> <p>Applications Alarm systems, light barriers, special sensors, analytics, optical communication</p>
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Miscellaneous Parameters

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Active area		A	0.62	mm ²
Temperature coefficient of I _D		T _C (I _D)	5	%/K
Operating temperature range		T _{amb}	-20 to +85	°C
Storage temperature range		T _{stg}	-30 to +100	°C
Soldering Temperature	t ≤ 3 s, 3 mm from case	T _{slid}	260	°C
Acceptance angle at 50% S _λ		φ	20	deg.

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Breakdown voltage ¹⁾	I _R = 10 μA	V _R	5			V
Dark current	V _R = 1 V	I _D		1.0	2.5	nA
Peak sensitivity wavelength	V _R = 0 V	λ _p		890		nm
Responsivity at λ _p	V _R = 0 V	S _λ	0.3	0.55		A/W
Sensitivity range at 10% ¹⁾	V _R = 0 V	λ _{min} , λ _{max}	800		960	nm
Spectral bandwidth at 50%	V _R = 0 V	Δλ _{0.5}		115		nm
Junction capacitance	V _R = 0 V	C _J		120		pF
Switching time (R _L = 50 Ω)	V _R = 1 V	t _r , t _f		200		ns

¹⁾for information only



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